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(54) **METHOD FOR FABRICATING SELECTOR
AND SEMICONDUCTOR DEVICE
INCLUDING THE SAME**

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(57)

ABSTRACT

A method for fabricating a selector may include: forming an insulating layer; doping the insulating layer with dopants by performing an ion implantation process; and performing a subsequent process to the insulating layer doped with the dopants for restoring damage caused by the ion implantation process.

Post Treatment

